

TENTATIVE

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN3C18FT

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

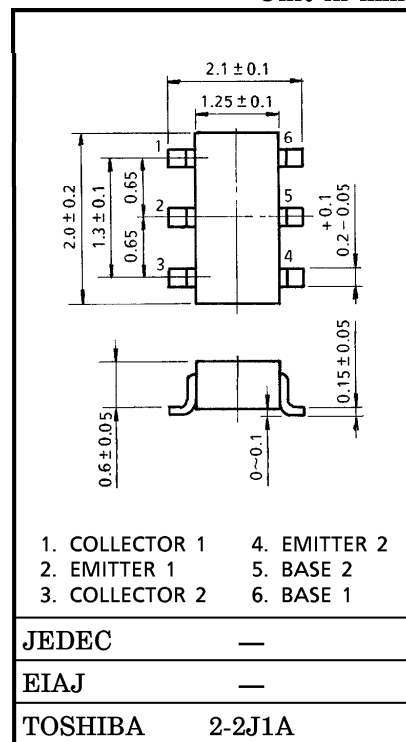
- TWO devices are built in to the super-thin and ultra super mini (6pins) package : TU6

MOUNTED DEVICES

	Q1 / Q2
Three-pins (SSM) mold products are corresponded	2SC5322

MAXIMUM RATINGS (Ta = 25°C)

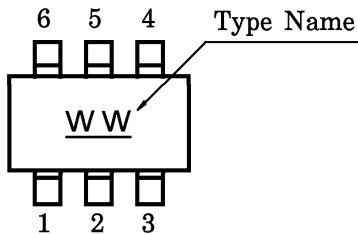
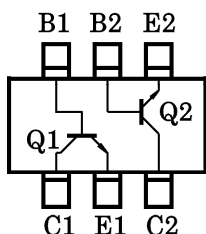
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	8	V
Collector-Emitter Voltage	V _{CEO}	5	V
Emitter-Base Voltage	V _{EBO}	1.5	V
Collector Current	I _C	10	mA
Base Current	I _B	5	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight : 0.008g

PIN ASSIGNMENT (TOP VIEW)

MARKING



961001EAA1

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ELECTRICAL CHARACTERISTICS (Q1, Q2) ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10\text{V}, I_E = 0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1\text{V}, I_C = 0$	—	—	1	μA
DC Current Gain	h_{FE} (Note 1)	$V_{CE} = 5\text{V}, I_C = 7\text{mA}$	50	—	250	—
Transition Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 7\text{mA}$	9	—	—	GHz
Insertion Gain	$ S_{21e} ^2$	$V_{CE} = 5\text{V}, I_C = 7\text{mA},$ $f = 2000\text{MHz}$	—	10	—	dB
Noise Figure	NF	$V_{CE} = 5\text{V}, I_C = 3\text{mA},$ $f = 2000\text{MHz}$	—	1.4	2.3	dB
Reverse Transfer Capacitance Q1	C_{re}	$V_{CB} = 5\text{V}, I_E = 0,$ $f = 1\text{MHz}$ (Note)	—	0.45	—	pF
Reverse Transfer Capacitance Q2	C_{re}		—	0.35	—	

(Note) C_{re} is measured by 3 terminal method capacitance bridge.